

Application Serial No. 10/615,708
Reply to Office Action of March 23, 2005

PATENT
Docket: CU-3283

Amendments To The Abstract

Clean Version

Please replace the Abstract of the Disclosure with the following paragraph:

In a silicon substrate having a contact hole in a device region, the contact resistance between the contact plug and the silicon substrate is reduced by preventing formation of an undesirable layer therebetween by treating the exposed surface of the substrate before forming the contact plug. Further, a two-layered contact plug consisting of a first contact plug layer having high impurity concentration and a second contact plug layer having low impurity concentration, on the interlayer insulating film including the exposed surface of the substrate. The interface between the silicon substrate and the contact plug is thermally treated at low temperature, and the first contact plug layer having high impurity concentration and the second contact plug layer having low impurity concentration, are formed, so that the resistance between the silicon substrate and the contact plug can be reduced, thereby increasing the operation speed of the device.